



PATENT
Customer No. 22,852
Attorney Docket No. 04329.2306

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
Yoshio OZAWA, et al.) Group Art Unit: 2826
Serial No.: 09/559,757) Examiner: Mondt, Johannes P.
Filed: April 27, 2000)
For: SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURE)
THEREOF)

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

Supplementary to the Request for Continued Examination (RCE) filed on May 29, 2002,
please amend the application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

Sub C1

1. (Twice Amended) A semiconductor device comprising:
a semiconductor substrate having a main plane in which a channel of a transistor is
formed, the semiconductor substrate comprising a first region and a second region defined in a
section taken along a direction of a channel length, the second region having a surface located
lower than that of the first region, and the second region being connected to the first region;
a gate insulating film formed on the first region and containing silicon, nitrogen and
oxygen;

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